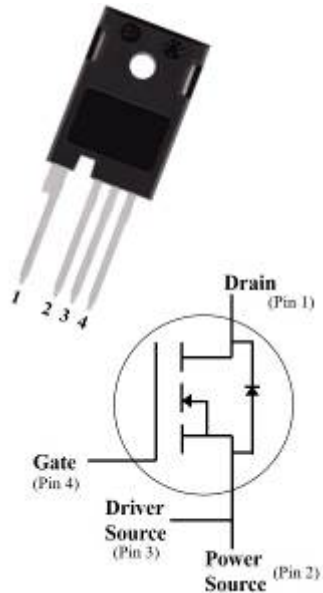


## Silicon Carbide Power MOSFET (N-Channel Enhancement)

$V_{DS}$	1200V
$I_D$ (25°C)	68A
$R_{DS(on)}$	30mΩ



### Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant

### Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### Mechanical Data

- **Package:** TO247-4L
- **Terminals:** Tin plated leads
- **Polarity:** As marked
- AEC-Q101 qualified

### ■Maximum Ratings ( $T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code			D212030NCFG2Q		
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	1200	$V_{GS}=0\text{ V}, I_D=100\mu\text{A}$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-8/+20	Absolute maximum values	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+18	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	$I_D$	A	68	$V_{GS}=18\text{V}, T_c=25^\circ\text{C}$	Fig.17
Continuous drain current @ $T_c=100^\circ\text{C}$			50	$V_{GS}=18\text{V}, T_c=100^\circ\text{C}$	
Pulsed drain current	$I_{D(pulsed)}$	A	100	Pulse width $t_p$ limited by $T_{j,max}$	Fig.22
Power Dissipation	$P_{TOT}$	W	333	$T_c=25^\circ\text{C}, T_j = 175^\circ\text{C}$	Fig.16
Power Dissipation			165	$T_c=100^\circ\text{C}, T_j = 175^\circ\text{C}$	
Operating junction and Storage temperature range	$T_j, T_{stg}$	$^\circ\text{C}$	-55 to +175		
Soldering temperature	$T_L$	$^\circ\text{C}$	260	1.6mm (0.063") from case for 10s	
Mounting torque	$T_M$	Nm	0.6	M3 screw Maximum of mounting process: 3	



# YJD212030NCFG2Q

## ■Static Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	V <sub>GS(th)</sub>	V	2.0	3.7	4.2	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =10mA	Fig.4, 11
				2.8		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =10mA, T <sub>j</sub> =175°C	
Drain source breakdown voltage	V <sub>(BR)DSS</sub>	V	1200			V <sub>GS</sub> =0V, I <sub>D</sub> =100uA	
Gate source leakage current	I <sub>GSS</sub>	nA			200	V <sub>GS</sub> =18V, V <sub>DS</sub> =0V	
Current drain source on-state resistance	R <sub>DS ON</sub>	mΩ		30	50	V <sub>GS</sub> =18V, I <sub>D</sub> =30A, T <sub>j</sub> =25°C	Fig.5, 6, 7
				50		V <sub>GS</sub> =18V, I <sub>D</sub> =30A, T <sub>j</sub> =175°C	
Internal gate resistance	R <sub>g</sub>	Ω		2.1		f=1MHz, V <sub>AC</sub> =25mV	
Transconductance	g <sub>fs</sub>	S		20		V <sub>DS</sub> =20V, I <sub>D</sub> =30A, T <sub>j</sub> =25°C	Fig.4
				18.5		V <sub>DS</sub> =20V, I <sub>D</sub> =30A, T <sub>j</sub> =175°C	

## ■Dynamic Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	C <sub>iss</sub>	pF		2995		V <sub>DS</sub> =1000V, V <sub>GS</sub> =0V, T <sub>j</sub> =25°C, f=1MHz, V <sub>AC</sub> =25mV	Fig.13, 14
Output capacitance	C <sub>oss</sub>			119			
Reverse capacitance	C <sub>rss</sub>			11.4			
Coss stored energy	E <sub>oss</sub>	uJ		130			Fig.15
Gate source charge	Q <sub>gs</sub>	nC		24		V <sub>DS</sub> =800V, V <sub>GS</sub> =-5/18V, I <sub>D</sub> =30A	Fig.12
Gate drain charge	Q <sub>gd</sub>			58			
Gate charge	Q <sub>g</sub>			127			

## ■Switching Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on switching energy	E <sub>on</sub>	uJ		685		V <sub>DD</sub> =800V, V <sub>GS</sub> =-5/+18V, I <sub>D</sub> =30A, R <sub>g</sub> =2.5Ω, L=200uH	Fig. 19, 20
Turn off switching energy	E <sub>off</sub>			78			
Turn on delay time	t <sub>d(on)</sub>	ns		60		V <sub>DD</sub> =800V, V <sub>GS</sub> =-5/+18V, I <sub>D</sub> =30A, R <sub>g</sub> =2.5Ω, L=200uH	Fig.21
Rise time	t <sub>r</sub>			140			
Turn off delay time	t <sub>d(off)</sub>			50			
Fall time	t <sub>f</sub>			42			



# YJD212030NCFG2Q

## ■Body diode characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V <sub>SD</sub>	V		3.5		V <sub>GS</sub> =-5V, I <sub>SD</sub> =15A, T <sub>j</sub> =25°C	Fig.8
				3.0		V <sub>GS</sub> =0V, I <sub>SD</sub> =15A, T <sub>j</sub> =175°C	Fig.9
Continuous diode forward current	I <sub>S</sub>	A		68		T <sub>c</sub> =25°C	
Reverse recovery time	t <sub>rr</sub>	nS		34		V <sub>R</sub> =800V, V <sub>GS</sub> =-5V, I <sub>SD</sub> =30A, di/dt=1428A/uS	
Reverse recovery charge	Q <sub>rr</sub>	nC		205			
Peak reverse recovery current	I <sub>rrm</sub>	A		14			

## ■Thermal Characteristics (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Typ.
Thermal resistance	R <sub>θJ-C</sub>	°C/W	0.45

## ■Typical Characteristics

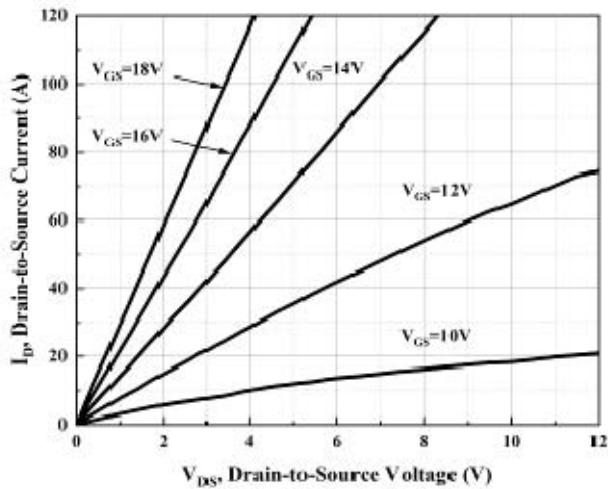


Figure 1. Output Characteristics T<sub>j</sub> = -55°C

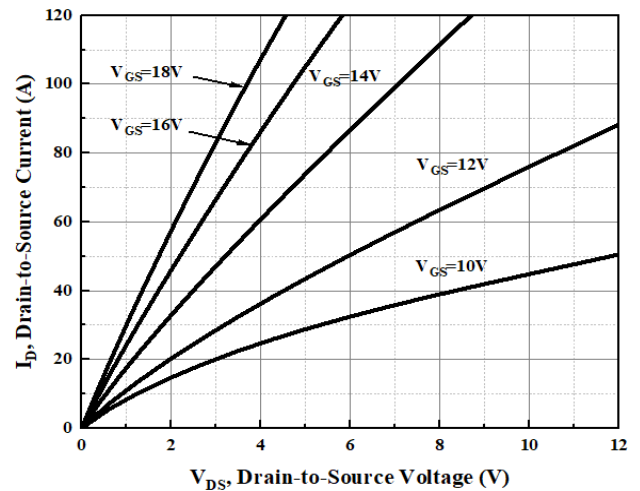


Figure2. Output Characteristics T<sub>j</sub> = 25°C



# YJD212030NCFG2Q

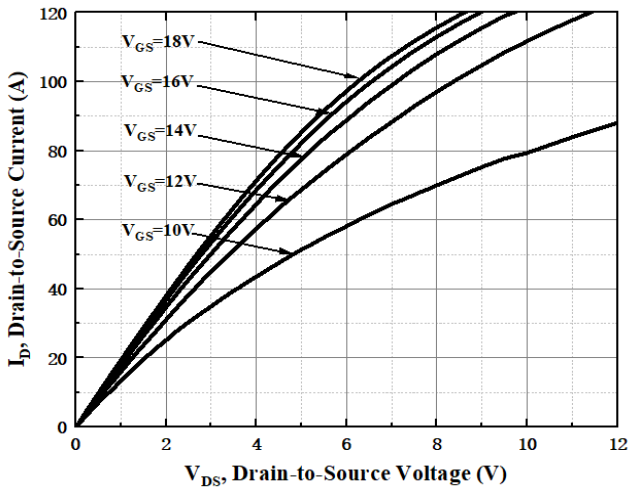


Figure 3. Output Characteristics  $T_j = 175^\circ\text{C}$

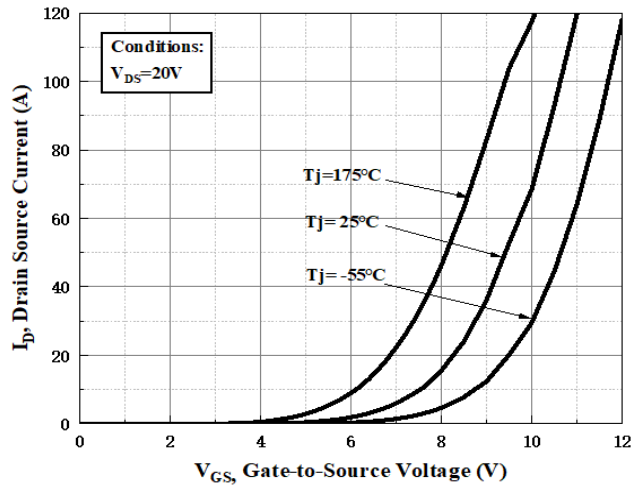


Figure 4. Transfer Characteristics for Various Junction Temperature

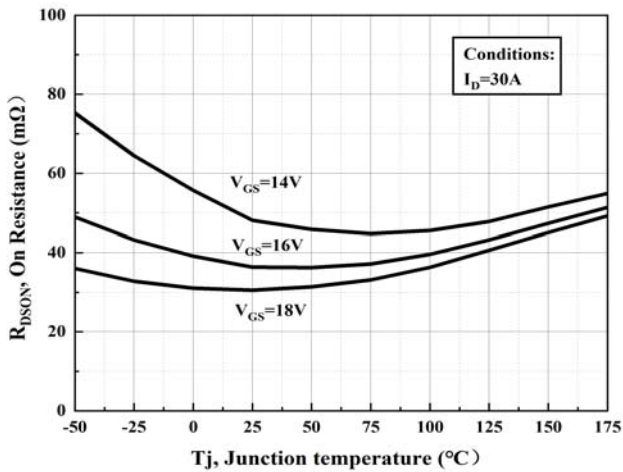


Figure 5. On-resistance vs. Temperature for Various Gate Voltage

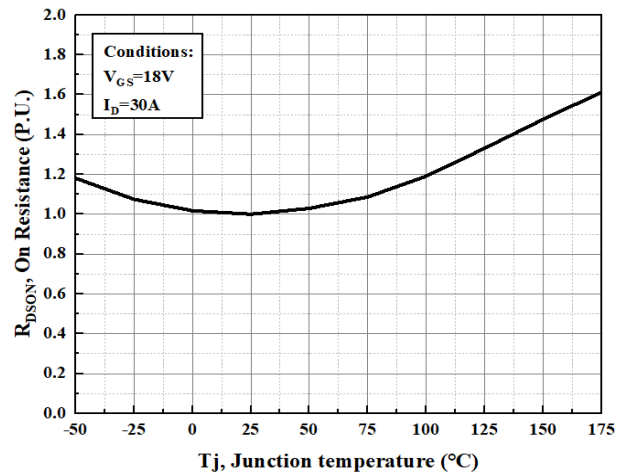


Figure 6. Normalized on-resistance vs. Temperature

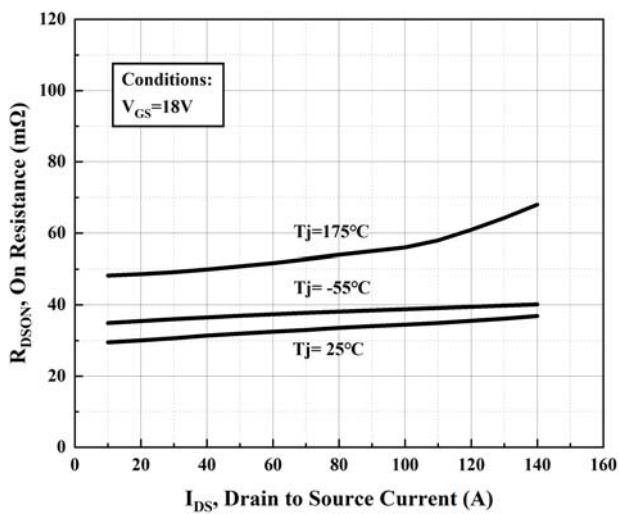


Figure 7. On-resistance vs. Drain Current

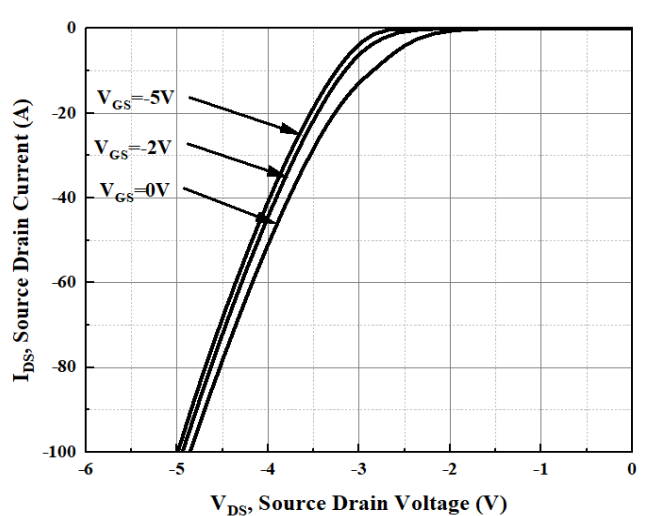


Figure 8. Body Diode Characteristic at  $T_j = 25^\circ\text{C}$



# YJD212030NCFG2Q

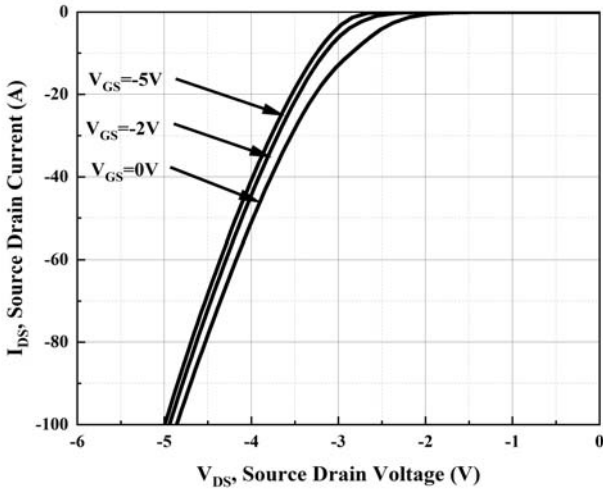


Figure 9. Body Diode Characteristic

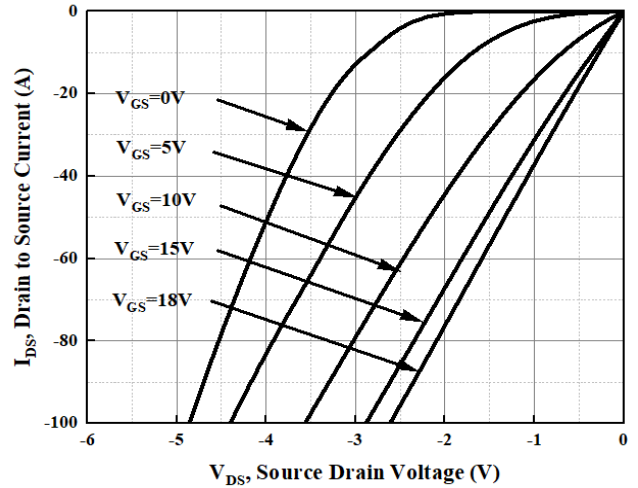


Figure 10. 3<sup>rd</sup> quadrant Characteristic at  $T_j = 25\text{ }^\circ\text{C}$

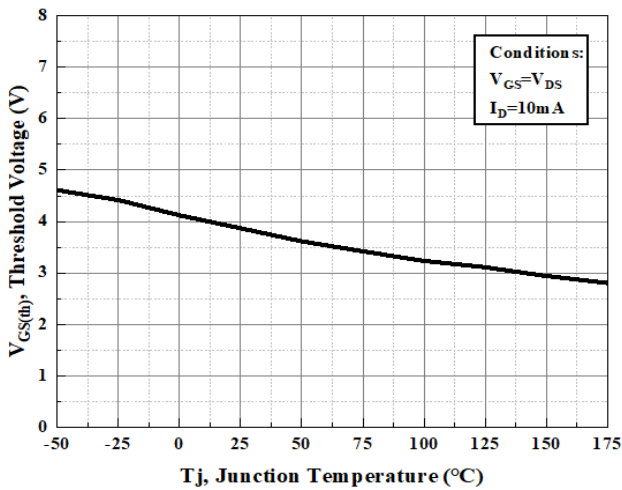


Figure 11. Threshold Voltage vs. Temperature

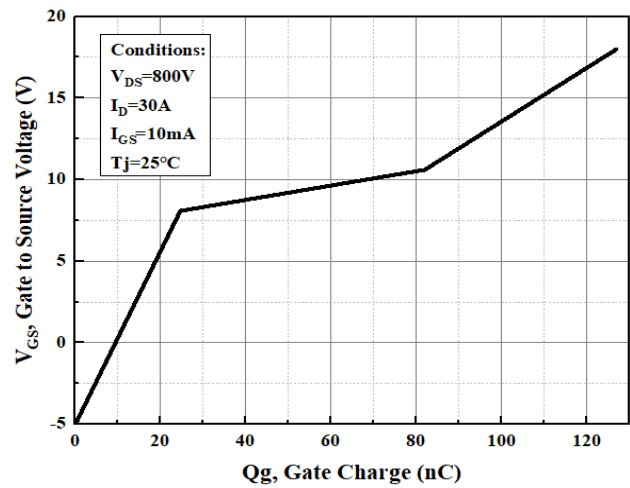


Figure 12. Gate Charge Characteristic

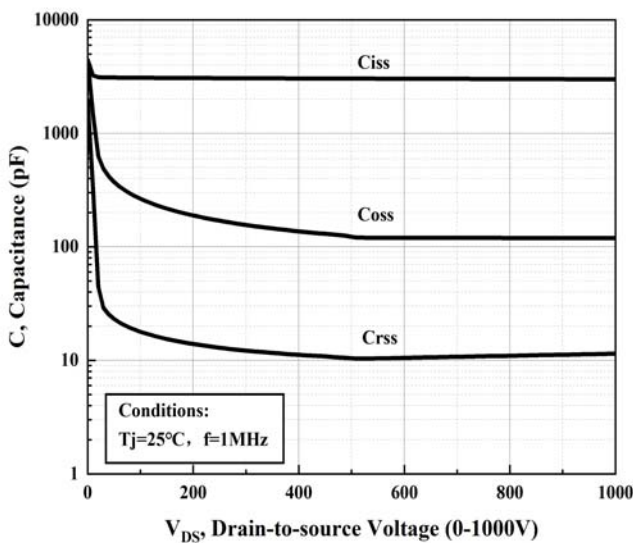


Figure 13. Capacitances vs. Drain Source Voltage (0-1000V)

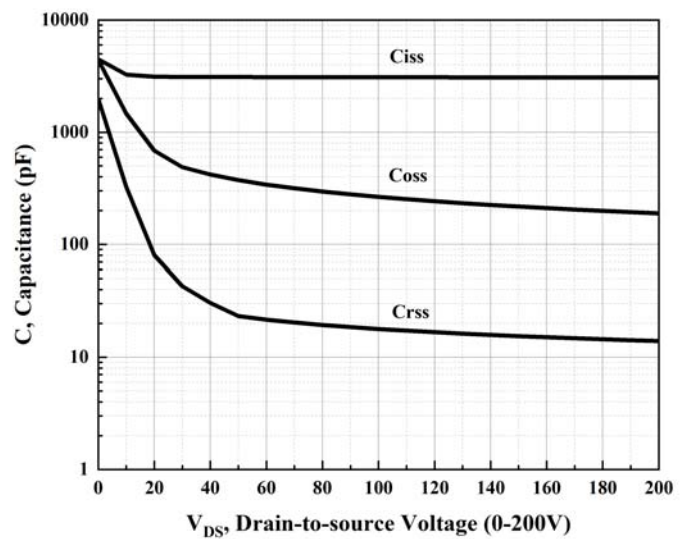


Figure 14. Capacitances vs. Drain Source Voltage (0-200V)



# YJD212030NCFG2Q

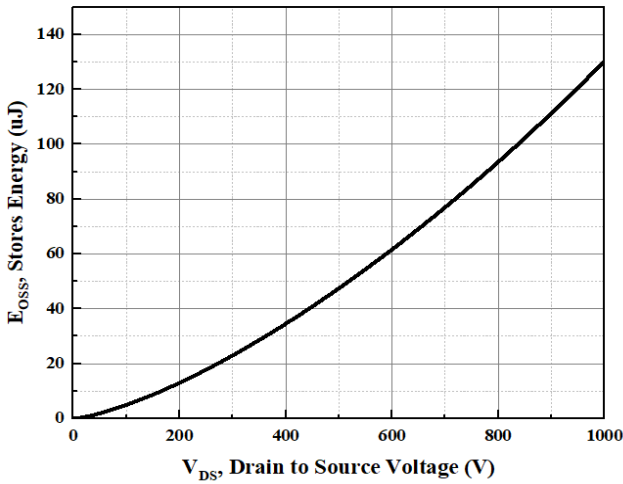


Figure 15. Output Capacitor Stored Energy

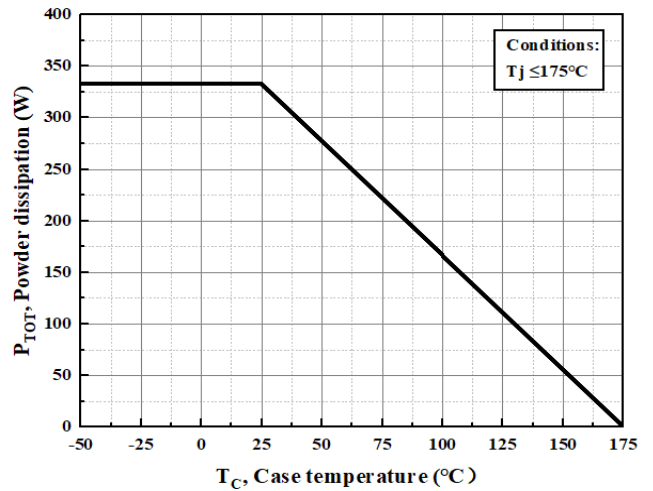


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

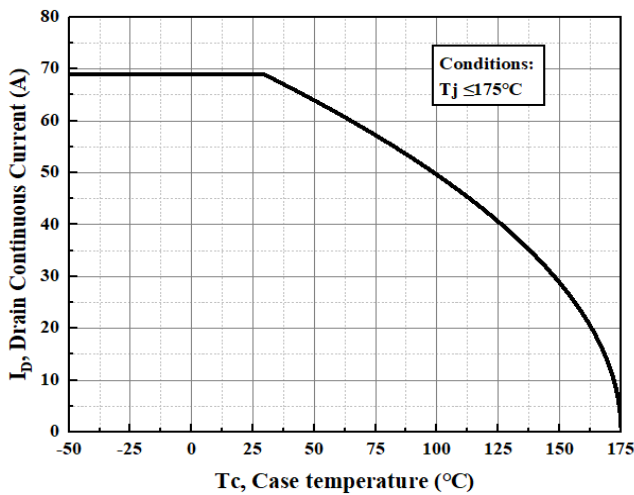


Figure 17. Continuous Drain Current Derating vs Case Temperature

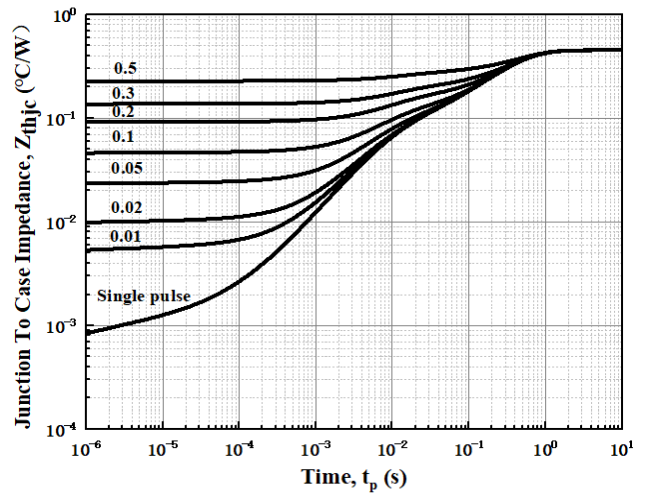


Figure 18 Transient Thermal Impedance (Junction - Case)

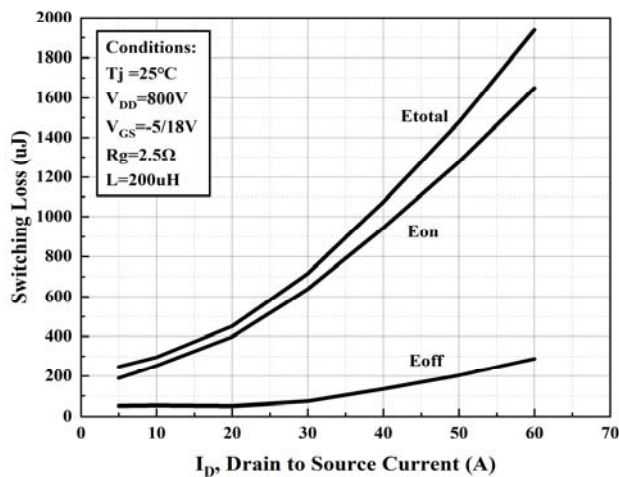


Figure 19. Clamped Inductive Switching Energy vs. Drain Current

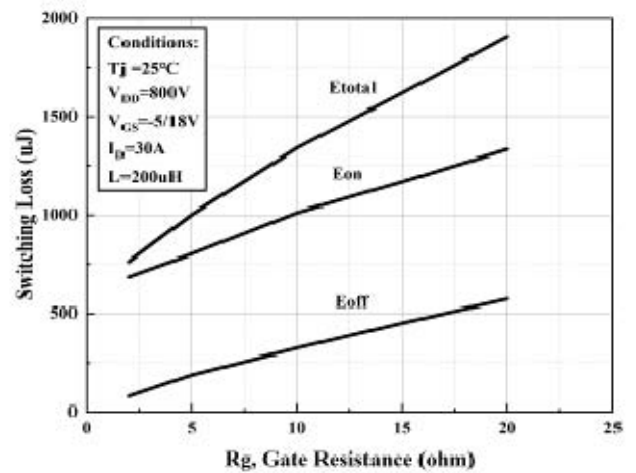


Figure 20. Clamped Inductive Switching Energy vs. Rg

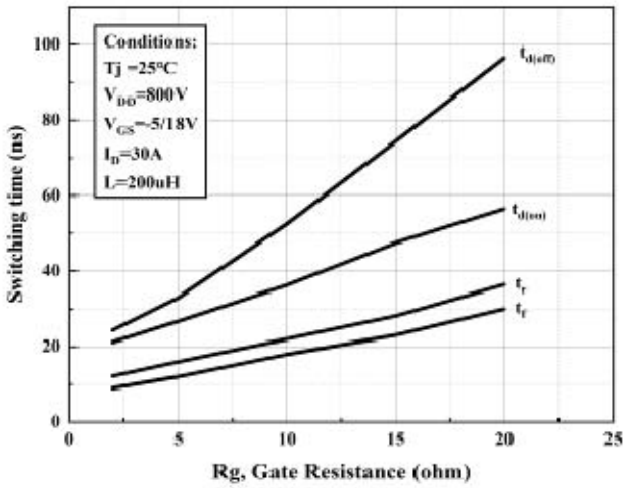


Figure 21. Switching Times vs. Rg

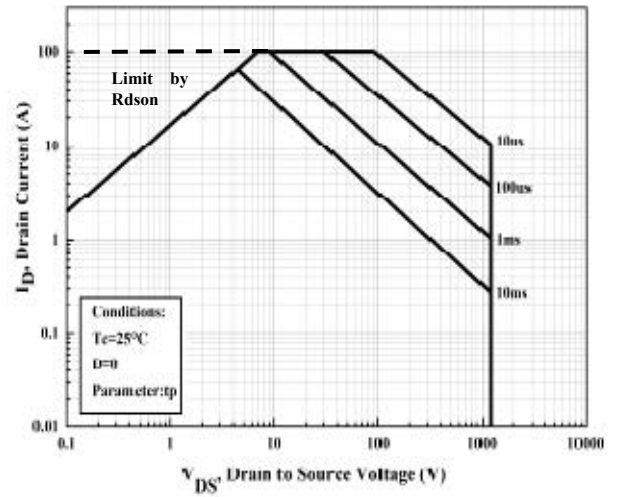


Figure 22. Safe Operating Area

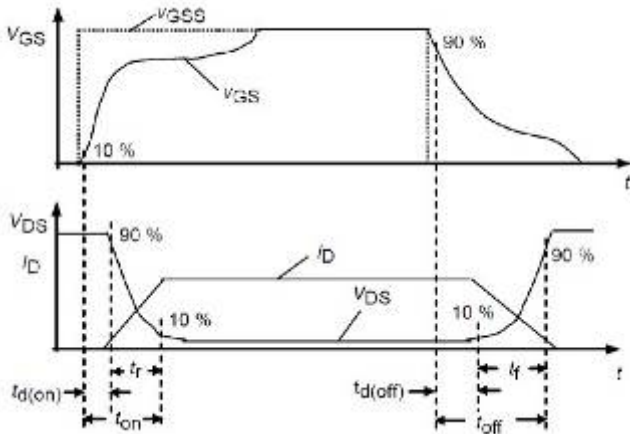


Figure 23. Switching Times Definition

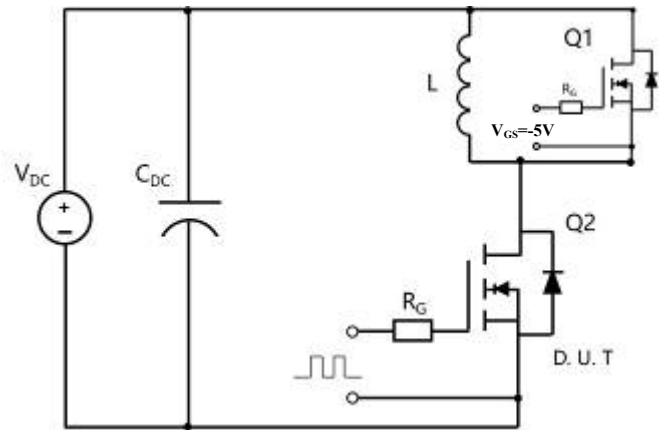
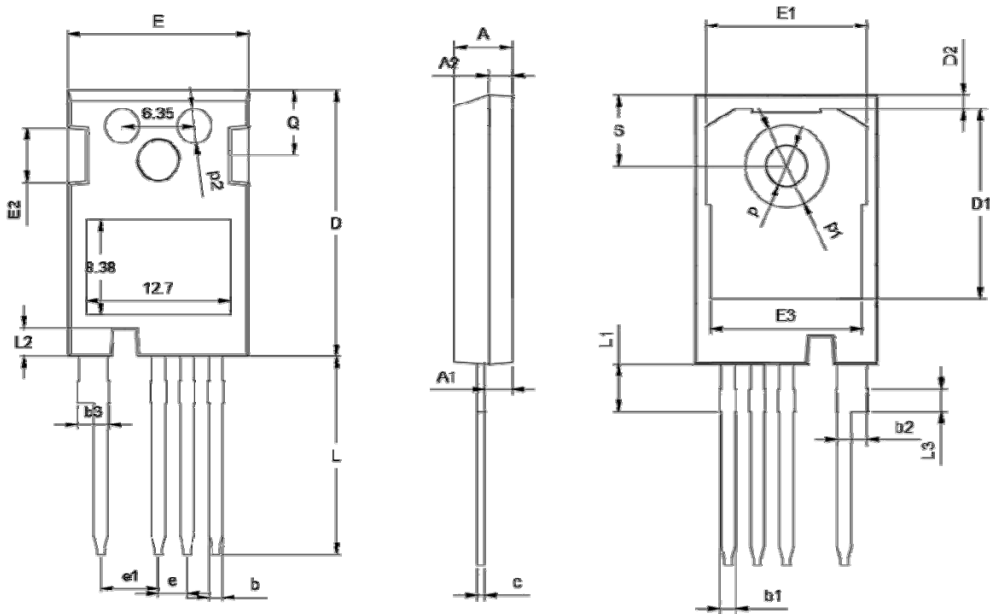


Figure 24. Clamped Inductive Switching Waveform Test Circuit



# YJD212030NCFG2Q

## ■Outline Dimensions



TO247-4L			
Dim	Min	Norm	Max
A	4.80	5.00	5.20
A1	2.30	2.40	2.50
A2	1.88	1.98	2.08
b	1.10	1.20	1.30
b1	1.20	/	1.50
b2	2.35	2.55	2.75
b3	2.45	/	2.85
c	0.55	0.60	0.65
D	23.3	23.45	23.6
D1	16.25	16.55	16.85
D2	1.00	/	1.30
e	TYP2.54		
e1	TYP5.06		
E	15.75	15.90	16.05
E1	13.80	/	14.20
E2	4.40	4.75	5.10
E3	13.00	/	13.45
L	17.34	17.49	17.64
L1	4.00	/	4.30
L2	2.35	/	2.65
L3	TYP1.98		
Q	5.60	5.80	6.00
S	6.05	/	6.30
p	TYP3.58		
p1	TYP7.18		
p2	TYP3.00		





## YJD212030NCFG2Q

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